Commercial Poly-Silicon Specifications

Here are the specification for poly-silicon from one of the worlds largest suppliers, Wacker Siltronic as they appear in the Internet in Nov. 2000.

PolySilicon

PolySilicon for Crucible Grov	ving		
Chip Size		mm	5 - 45 / 20 - 65 / 20 - 150
Surface			smooth, etched
Surface Metal Concentration	Monitor: Iron	pptw	< 500
Bulk Element Concentration	Donors (P, As, Sb)	ppta	< 150
	Acceptors (B, Al)	ppta	< 50
	Carbon	ppba	< 100
PolySilicon Ingots for Float Z	one Growing		
ngot Length		mm	600 -1,850
Diameter		mm	90 - 105 / 118 - 135 / 135 - 154
Surface			smooth, etched
Bulk Element Concentration	Donors (P, As, Sb)	ppta	< 300
	Acceptors (B, Al)	ppta	< 100
	Carbon	ppba	< 200
olySilicon Ingots for Crucib	le Growing		
ngot Length		mm	320 - 980
Diameter		mm	90 - 115 / 115 - 135
Surface			smooth, etched
Bulk Element Concentration	Donors (P, As, Sb)	ppta	< 300
	Acceptors (B, Al)	ppta	< 100
	Carbon	ppba	< 200
Solar Grade PolySilicon for C	rucible Growing/Casting		
Chip Size		mm	0 - 15 / 5 - 160
Bulk Element Concentration	Donors (P, As, Sb)	ppta	< 300
	Acceptors (B, Al)	ppta	< 100
	Carbon	ppba	< 200
Cleaning			none

Here some productio information:

According to "Solid State Technlogy" July 2005, the productio numbers are as follows:

- Total production 2005: 26.000.000 kg; about 2/3 for miocroelectronics, 1/3 for photovoltaics.
- Expected production 2006: 29.000.000 kg.

Expected shortfalls:

- 2005: 4.000.000 kg
- 2006: 6.000.000 kg.
- 2007: **12.000.000 kg**.
- 2008: 20.000 000 kg.

The expected shortfalls result to a large extent from a growthrate of **30** % for photovoltaics and from technical and financial difficulties to crank up püroduction at a high reate. However, alternative processes solar **Si** production are expected to come on-line in 2006.

Notice: The "w " or "a" behind the concentration denotes w eigth or atomic parts per m = million, b = billion, t = trillion.